AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A resist composition for an electron beam or EUV, ~~wherein~~ comprising an organic solvent ~~comprising, as a principal component, one or more compounds~~ comprising a compound selected from ~~a~~ the group consisting of propylene glycol monomethyl ether (PGME), methyl amyl ketone (MAK), butyl acetate (BuOAc)[[,]] and 3-methyl methoxy propionate (MMP) ~~is used as a resist solvent~~.

2. (Currently amended) A resist composition for an electron beam or EUV according to claim 1, ~~which exhibits characteristics that satisfy a~~ wherein said composition satisfies formula I shown below:

[Film thickness (1) – Film thickness(2)]/(150-130)(Å /°C)≤0.2 (Å /°C) (I)

[wherein, said film thickness (1) is a film thickness following application of said resist composition to a substrate in sufficient quantity to generate a film thickness of 2300 Å±10% and subsequent heating at 130°C for 90 seconds, and said film thickness (2) is a film thickness following application of said resist composition to a substrate in sufficient quantity to generate a film thickness of 2300 Å±10% and subsequent heating at 150°C for 90 seconds].

3. (Original) A resist composition for an electron beam or EUV according to claim 1, wherein a degree of variation in total pressure of an atmosphere inside an exposure system between a state prior to exposure and a state following exposure is less than 4.0×10^{-5} Pa.

4. (Currently amended) A resist composition for an electron beam or EUV according to claim 1, further comprising a compound (A) having acid dissociable, dissolution inhibiting groups, and an acid generator (B).

5. (Currently amended) A resist composition for an electron beam or EUV according to claim 4, further comprising a nitrogen-containing compound (C) ~~in addition to said components (A) and (B)~~.

6. (Currently amended) A method of forming a resist pattern, comprising the steps of applying a resist composition for an electron beam or EUV according to any one of claim 1 through claim 5 to a substrate, ~~conducting a prebake~~ prebaking said substrate, ~~conducting selective exposure~~ selectively exposing or ~~direct~~ directly patterning said substrate with an electron beam or EUV in a vacuum, ~~performing PEB (~~post exposure baking[[)]] said substrate, and ~~then~~ conducting alkali developing to form said resist pattern.